

IN THE SPECIFICATION:

Page 1, after the heading "DESCRIPTION" please insert the following:

--RELATED APPLICATIONS

A1

This application is a divisional application of U.S. application Serial No. 09/519,897,
filed on March 6, 2000.--

IN THE CLAIMS:

Please cancel Claims 1-22, without prejudice or disclaimer, and add the following new claims:

--25. The electrical contact of Claim 23 wherein said silicon-containing semiconductor material comprises single crystal Si, polycrystalline Si, SiGe, amorphous Si or a silicon-on-insulator (SOI).

26. The electrical contact of Claim 23 wherein said metal of said disilicide is Co and said metal silicide is Co disilicide.

27. The electrical contact of Claim 23 wherein said metal of said disilicide is Ti and said metal silicide is TiSi_2 .

28. The electrical contact of Claim 27 wherein said TiSi_2 is in the C54 phase.

29. The electrical contact of Claim 23 further comprising an oxide layer present near a surface of said substrate.

30. The electrical contact of Claim 29 wherein said oxide layer has a thickness of from about 0.1 to about 3.0 nm.

31. The electrical contact of Claim 23 wherein said substrate is doped.